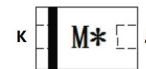


WSB5546N
0.2A, Schottky Barrier Diode
[Http://www.sh-willsemi.com](http://www.sh-willsemi.com)
Features

- Low reverse current
- 0.2A Average rectified forward current
- Standard products are Pb-free and Halogen-free


DFN1006-2L

Circuit

Marking
Absolute maximum ratings

Parameter	Symbol	Value	Unit
Reverse voltage (repetitive peak)	V_{RM}	40	V
Reverse voltage (DC)	V_R	40	V
Average rectified forward current	I_O	0.2	A
Peak forward current ⁽¹⁾	I_{FSM}	3	A
Junction temperature	T_J	150	°C
Operating temperature	T_{opr}	-40 ~ 150	°C
Storage temperature	T_{stg}	-55 ~ 150	°C

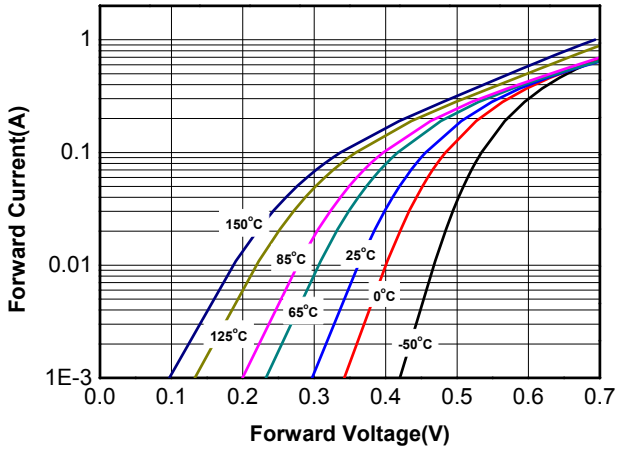
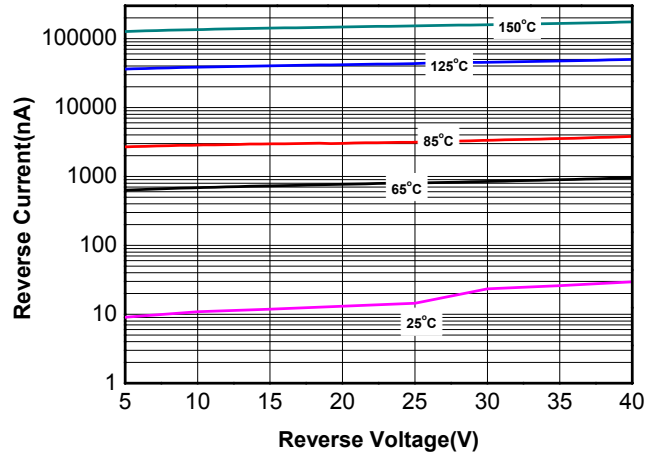
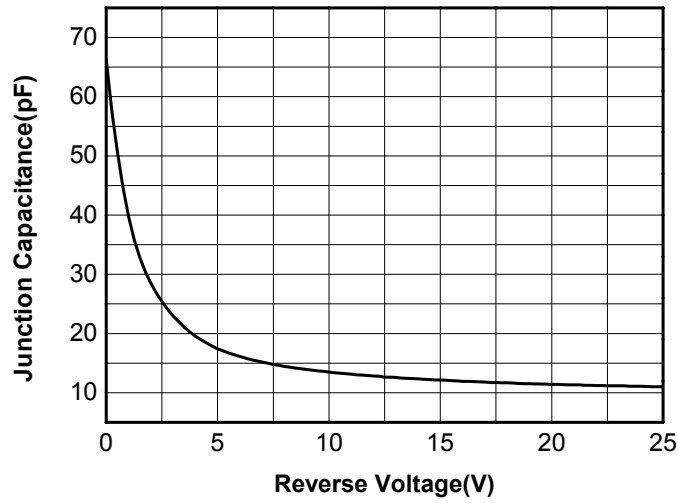
Electronics characteristics ($T_A=25^{\circ}C$)

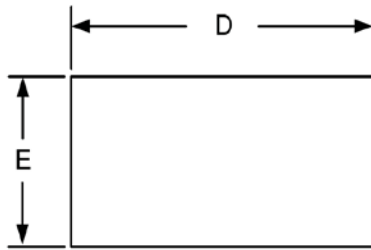
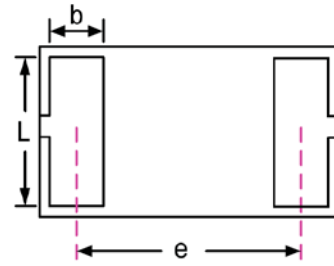
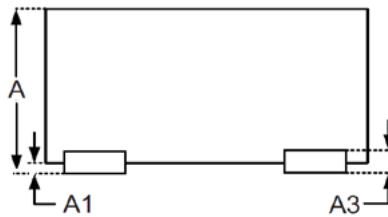
Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Forward voltage ⁽²⁾	V_F	$I_F=0.2A$	-	0.51	0.60	V
Reverse current	I_R	$V_R=10V$	-	-	0.5	uA
		$V_R=40V$	-	-	1	uA
Junction capacitance	C_J	$V_R=4V, F=1MHz$	-	17	-	pF
Thermal resistance	$R_{\theta(j-a)}$	Junction to ambient	-	-	500	K/W

Order Informations

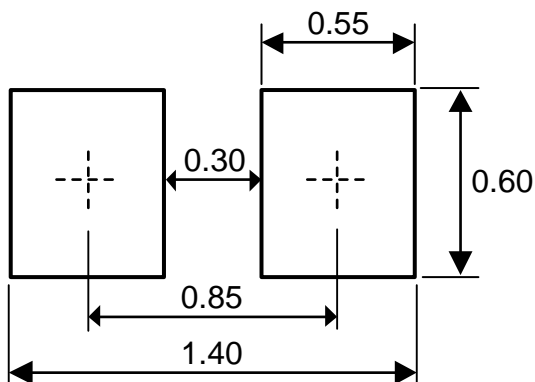
Device	Package	Marking	Shipping
WSB5546N-2/TR	DFN1006-2L	M* ⁽³⁾	10000/Reel&Tape

Note 1: Pulse Width=8.3ms, Single half-sine Pulse;
Note 2: Pulse Width<380us;
Note 3:* = Month code (A~Z); M = Device code;

Typical characteristics (Ta=25°C, unless otherwise noted)

Forward voltage vs. Forward current

Reverse current vs. Reverse voltage

Junction capacitance vs. Reverse voltage

Package outline dimensions
DFN1006-2L

Top View

Bottom View

Side View

Symbol	Dimensions in millimeter		
	Min.	Typ.	Max.
A	0.40	-	0.50
A1	0.00	-	0.05
A3	0.125 Ref.		
D	0.95	1.00	1.05
E	0.55	0.60	0.65
b	0.20	0.25	0.30
L	0.45	0.50	0.55
e	0.65 Typ.		

Recommend land pattern (Unit: mm)

Notes:

This recommended land pattern is for reference purposes only. Please consult your manufacturing group to ensure your PCB design guidelines are met.